

PHASE CONTROL THYRISTORS

Hockey Puk Version

Features

- Center amplifying gate
- Metal case with ceramic insulator
- International standard case TO-200AB (E-PUK)

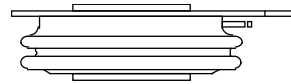
Typical Applications

- DC motor controls
- Controlled DC power supplies
- AC controllers

Major Ratings and Characteristics

Parameters	ST330C..C	Units
$I_{T(AV)}$	720	A
@ T_{hs}	55	°C
$I_{T(RMS)}$	1420	A
@ T_{hs}	25	°C
I_{TSM}	@ 50Hz	9000
	@ 60Hz	9420
I^2t	@ 50Hz	405
	@ 60Hz	370
V_{DRM}/V_{RRM}	400 to 1600	V
t_q typical	100	μs
T_J	- 40 to 125	°C

720A



case style TO-200AB (E-PUK)

ST330C..C Series

Bulletin I25155 rev. C 04/00

International
IR Rectifier**ELECTRICAL SPECIFICATIONS****Voltage Ratings**

Type number	Voltage Code	V_{DRM}/V_{RRM} , max. repetitive peak and off-state voltage V	V_{RSM} , maximum non-repetitive peak voltage V	I_{DRM}/I_{RRM} max. @ $T_J = T_J \text{ max}$ mA
ST330C..C	04	400	500	50
	08	800	900	
	12	1200	1300	
	14	1400	1500	
	16	1600	1700	

On-state Conduction

Parameter	ST330C..C	Units	Conditions
$I_{T(AV)}$ Max. average on-state current @ Heatsink temperature	720 (350) 55 (75)	A °C	180° conduction, half sine wave double side (single side) cooled
$I_{T(RMS)}$ Max. RMS on-state current	1420	A	DC @ 25°C heatsink temperature double side cooled
I_{TSM} Max. peak, one-cycle non-repetitive surge current	9000		t = 10ms No voltage
	9420		t = 8.3ms reapplied
	7570		t = 10ms 100% V_{RRM}
	7920		t = 8.3ms reapplied
I^2t Maximum I^2t for fusing	405	KA ² s	t = 10ms No voltage
	370		t = 8.3ms reapplied
	287		t = 10ms 100% V_{RRM}
	262		t = 8.3ms reapplied
$I^2\sqrt{t}$ Maximum $I^2\sqrt{t}$ for fusing	4050	KA ² √s	t = 0.1 to 10ms, no voltage reapplied
$V_{T(TO)1}$ Low level value of threshold voltage	0.91	V	$(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}), T_J = T_J \text{ max.}$
$V_{T(TO)2}$ High level value of threshold voltage	0.92		$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ max.}$
r_{t1} Low level value of on-state slope resistance	0.58	mΩ	$(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}), T_J = T_J \text{ max.}$
r_{t2} High level value of on-state slope resistance	0.57		$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ max.}$
V_{TM} Max. on-state voltage	1.96	V	$I_{pk} = 1810A, T_J = T_J \text{ max, } t_p = 10ms \text{ sine pulse}$
I_H Maximum holding current	600	mA	$T_J = 25^\circ C$, anode supply 12V resistive load
I_L Typical latching current	1000		

Switching

Parameter	ST330C..C	Units	Conditions
di/dt Max. non-repetitive rate of rise of turned-on current	1000	A/μs	Gate drive 20V, 20Ω, $t_i \leq 1\mu s$ $T_J = T_J \text{ max, anode voltage} \leq 80\% V_{DRM}$
t_d Typical delay time	1.0	μs	Gate current 1A, $di_g/dt = 1A/\mu s$ $V_d = 0.67\% V_{DRM}, T_J = 25^\circ C$
t_q Typical turn-off time	100		$I_{TM} = 550A, T_J = T_J \text{ max, } di/dt = 40A/\mu s, V_R = 50V$ $dv/dt = 20V/\mu s, \text{ Gate } 0V \text{ } 100\Omega, t_p = 500\mu s$

Blocking

Parameter	ST330C..C	Units	Conditions
dv/dt Maximum critical rate of rise of off-state voltage	500	V/ μ s	$T_J = T_J$ max. linear to 80% rated V_{DRM}
I_{RRM} I_{DRM} Max. peak reverse and off-state leakage current	50	mA	$T_J = T_J$ max, rated V_{DRM}/V_{RRM} applied

Triggering

Parameter	ST330C..C	Units	Conditions
P_{GM} Maximum peak gate power	10.0	W	$T_J = T_J$ max, $t_p \leq 5ms$
$P_{G(AV)}$ Maximum average gate power	2.0		$T_J = T_J$ max, $f = 50Hz$, $d\% = 50$
I_{GM} Max. peak positive gate current	3.0	A	$T_J = T_J$ max, $t_p \leq 5ms$
$+V_{GM}$ Maximum peak positive gate voltage	20	V	$T_J = T_J$ max, $t_p \leq 5ms$
$-V_{GM}$ Maximum peak negative gate voltage	5.0		
I_{GT} DC gate current required to trigger	TYP. 200	mA	$T_J = -40^\circ C$ $T_J = 25^\circ C$ $T_J = 125^\circ C$ Max. required gate trigger/ current/ voltage are the lowest value which will trigger all units 12V anode-to-cathode applied
	MAX. -		
	100		
	50		
V_{GT} DC gate voltage required to trigger	2.5	V	$T_J = -40^\circ C$ $T_J = 25^\circ C$ $T_J = 125^\circ C$
	1.8		
	1.1		
I_{GD} DC gate current not to trigger	10	mA	$T_J = T_J$ max Max. gate current/voltage not to trigger is the max. value which will not trigger any unit with rated V_{DRM} anode-to-cathode applied
V_{GD} DC gate voltage not to trigger	0.25	V	

Thermal and Mechanical Specification

Parameter	ST330C..C	Units	Conditions
T_J Max. operating temperature range	-40 to 125	$^\circ C$	
T_{stg} Max. storage temperature range	-40 to 150		
R_{thJ-hs} Max. thermal resistance, junction to heatsink	0.09 0.04	K/W	DC operation single side cooled DC operation double side cooled
R_{thC-hs} Max. thermal resistance, case to heatsink	0.02 0.01	K/W	DC operation single side cooled DC operation double side cooled
F Mounting force, $\pm 10\%$	9800 (1000)	N (Kg)	
wt Approximate weight	83	g	
Case style	TO - 200AB (E-PUK)		See Outline Table

ST330C..C Series

Bulletin I25155 rev.C 04/00

ΔR_{thJ-hs} Conduction

(The following table shows the increment of thermal resistance R_{thJ-hs} when devices operate at different conduction angles than DC)

Conduction angle	Sinusoidal conduction		Rectangular conduction		Units	Conditions
	Single Side	Double Side	Single Side	Double Side		
180°	0.012	0.011	0.008	0.007	K/W	$T_J = T_{J \text{ max.}}$
120°	0.014	0.012	0.014	0.013		
90°	0.017	0.015	0.019	0.017		
60°	0.025	0.022	0.026	0.023		
30°	0.043	0.036	0.043	0.037		

Ordering Information Table

Device Code

ST	33	0	C	16	C	1	
1	2	3	4	5	6	7	8

1

 - Thyristor

2

 - Essential part number

3

 - 0 = Converter grade

4

 - C = Ceramic Puk

5

 - Voltage code: Code x 100 = V_{RRM} (See Voltage Rating Table)

6

 - C = Puk Case TO-200AB (E-PUK)

7

 - 0 = Eyelet terminals (Gate and Auxiliary Cathode Unsoldered Leads)
1 = Fast-on terminals (Gate and Auxiliary Cathode Unsoldered Leads)
2 = Eyelet terminals (Gate and Auxiliary Cathode Soldered Leads)
3 = Fast-on terminals (Gate and Auxiliary Cathode Soldered Leads)

8

 - Critical dv/dt: None = 500V/ μ sec (Standard selection)
L = 1000V/ μ sec (Special selection)

Outline Table

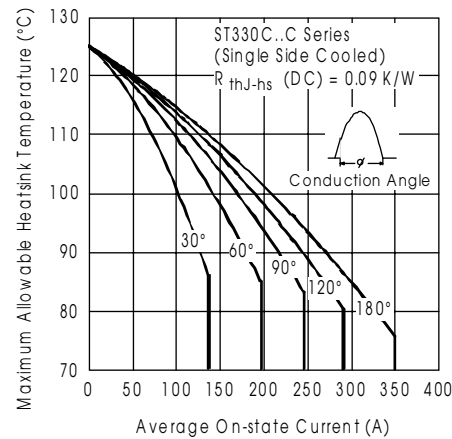
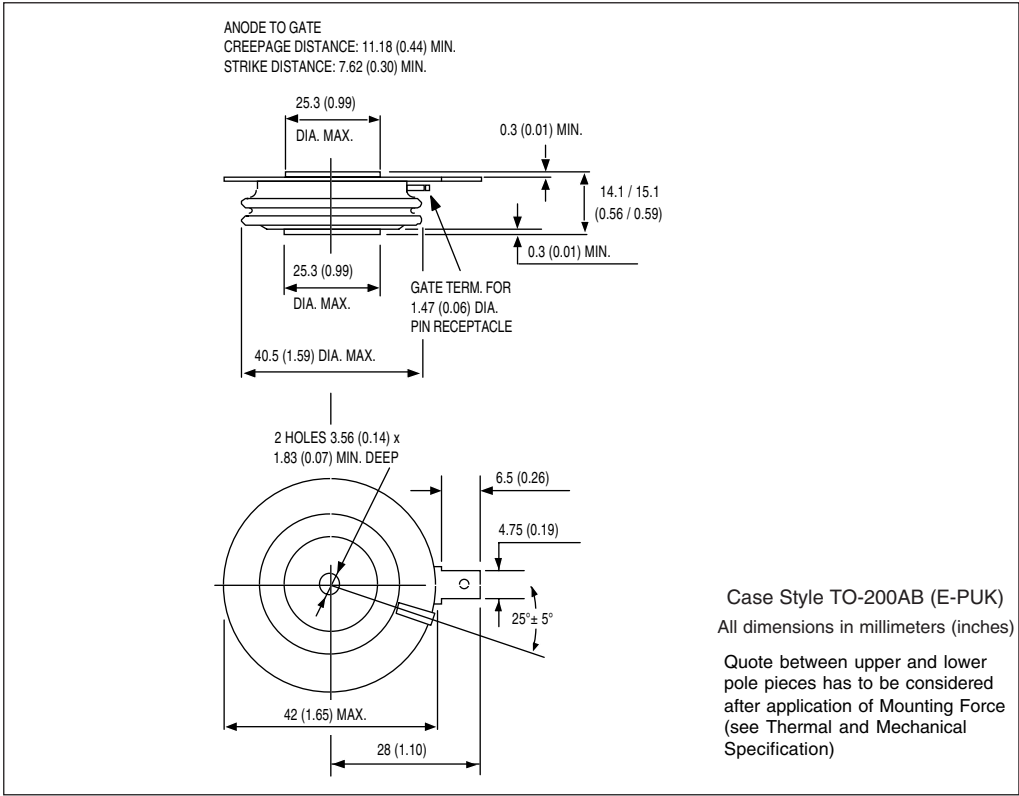


Fig. 1 - Current Ratings Characteristics

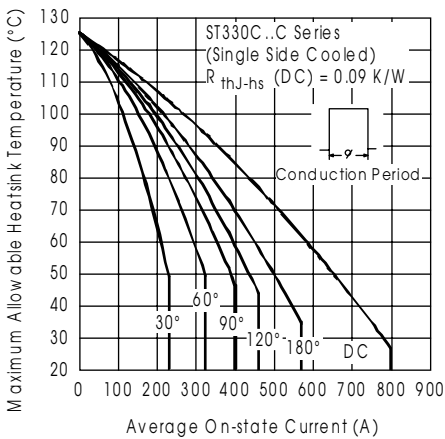


Fig. 2 - Current Ratings Characteristics

ST330C..C Series

Bulletin I25155 rev. C 04/00

International
IRF Rectifier

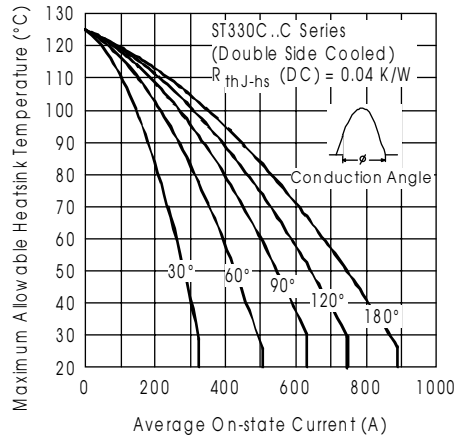


Fig. 3 - Current Ratings Characteristics

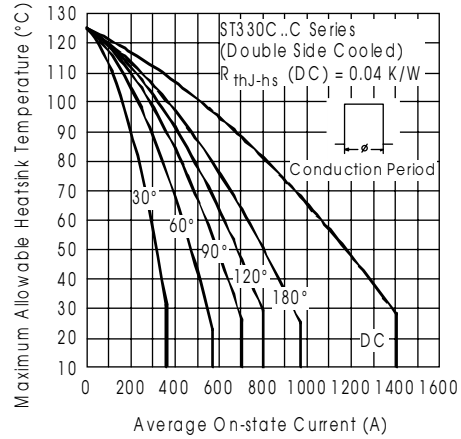


Fig. 4 - Current Ratings Characteristics

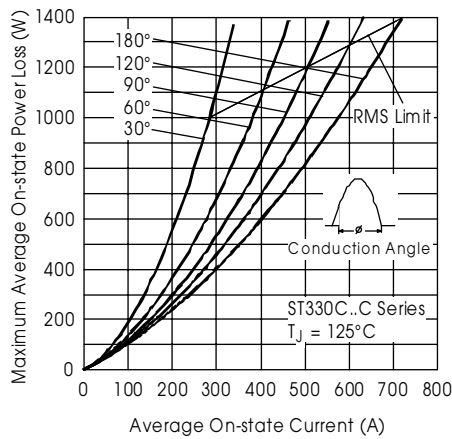


Fig. 5 - On-state Power Loss Characteristics

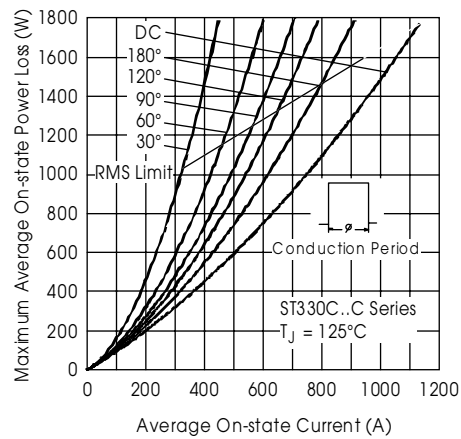


Fig. 6 - On-state Power Loss Characteristics

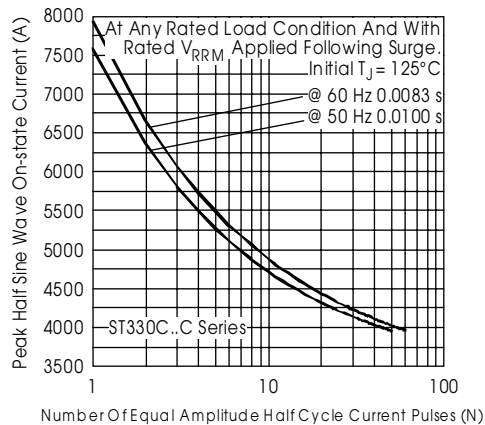


Fig. 7 - Maximum Non-Repetitive Surge Current
Single and Double Side Cooled

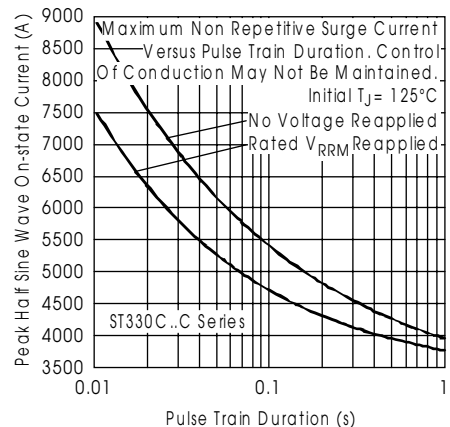


Fig. 8 - Maximum Non-Repetitive Surge Current
Single and Double Side Cooled

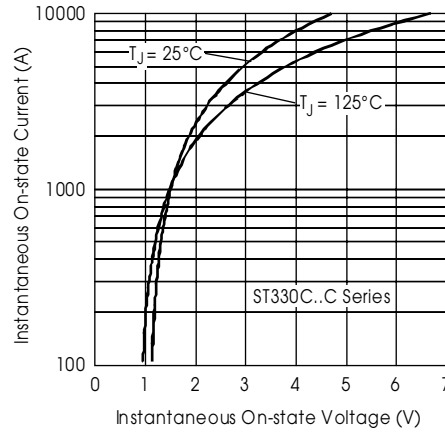


Fig. 9 - On-state Voltage Drop Characteristics

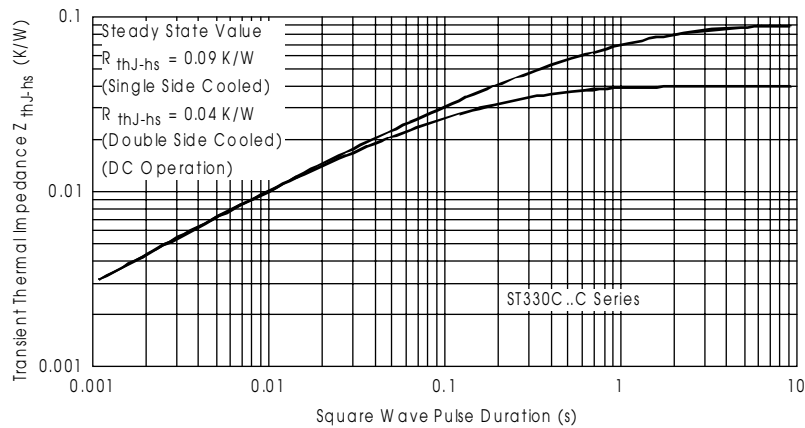


Fig. 10 - Thermal Impedance Z_{thJ-hs} Characteristics

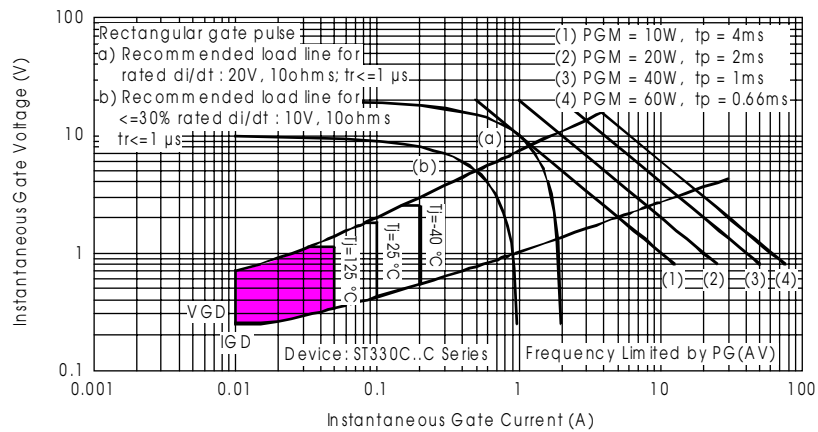


Fig. 11 - Gate Characteristics

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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